

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A magnetic memory fabricated on a semiconductor substrate comprising:
a plurality of magnetic tunneling junctions, each of the plurality of magnetic tunneling junctions including a first ferromagnetic layer, a second ferromagnetic layer and an insulating layer between the first ferromagnetic layer and the second ferromagnetic layer; and
a plurality of shields for magnetically shielding the plurality of magnetic tunneling junctions, at least a portion of the plurality of shields having a high moment and a high permeability and being conductive, the plurality of shields being electrically isolated from the plurality of magnetic tunneling junctions, the plurality of magnetic tunneling junctions being between the plurality of shields.
2. (Original) The magnetic memory of claim 1 wherein a first shield of the plurality of shields includes a first magnetic layer having a first easy access and a second magnetic layer having a second easy axis perpendicular to the first easy access.
3. (Original) The magnetic memory of claim 2 wherein a second shield of the plurality of shields includes a third magnetic layer having a third easy access and a fourth magnetic layer having a fourth easy axis perpendicular to the fourth easy access.

4. (Original) The magnetic memory of claim 1 wherein the plurality of shields include FeTaN.

5. (Original) The magnetic memory of claim 1 wherein the plurality of shields include FeAlN.

6. (Original) The magnetic memory of claim 1 wherein the plurality of shields include FeCrN.

7. (Original) The magnetic memory of claim 1 wherein the plurality of shields include a material having a saturation magnetization of greater than or equal to 850 memu/cm^3 .

8. (Original) The magnetic memory of claim 1 wherein the plurality of shields include a material having a saturation magnetization of greater than or equal to 1750 memu/cm^3 .

9. (Original) The magnetic memory of claim 7 wherein the material has an anisotropy field of less than or equal to thirty Oe.

10. (Original) The magnetic memory of claim 7 further comprising:
a plurality of semiconductor device coupled to the plurality of magnetic memory cells and residing between the plurality shields.

11. (Canceled)

12. (Canceled)

13. (Canceled)

14. (Canceled)

15. (Canceled)

16. (Canceled)

17. (Canceled)

18. (Canceled)

19. (Canceled)

20. (Canceled)

21. (Canceled)